

PATENT APPLICATION

Sheet 1 of 5

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 200210175-1	APPLICATION NO. 10/619639	CONFIRMATION NO.
	APPLICANT Martha A. Truninger et al.	FILING DATE 7/15/2003	GROUP Herewith
			UNKN. 2853

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	1A 5,385,635	01/1995	O'Neill	—
	1B 5,387,314	02/1995	Baughman et al.	—
	1C 5,393,711	02/1995	Ballas et al.	—
	1D 5,441,593	08/1995	Baughman et al.	—
	1E 5,498,312	03/1996	Laermer et al.	—
	1F 5,501,893	03/1996	Laermer et al.	—
	1G 5,526,454	06/1996	Mayer	—
	1H 5,541,140	07/1998	Goebel et al.	—
	1I 5,716,533	02/1998	O'Neill et al.	—
	1J 5,756,901	05/1998	Kurle et al.	—
	1K 5,870,123	02/1999	Lorenze, Jr. et al.	—

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	1L WO 9837577	08/1998	Bosch GMBH	—	
	1M WO 0023376	04/2000	Bosch GMBH	—	
	1N EP 0865151A2	09/1998	Hewlett-Packard Co.	—	
	1O EP 0886307A2	12/1998	Canon Kabushiki	—	
	1P EP 0978832A2	02/2000	Hewlett-Packard Co.	—	

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	1Q	"Cryogenic Etching of Deep Narrow Trenches In Silicon"; by: Aachboun et al.; Journal Of Vacuum Science & Technology A; Vol. 18, No. 4; pt. 1-2; July-Aug. 2000; Abstract Only.
	1R	"An Array of Hollow Microcapillaries For The Controlled Injection of Genetic Materials Into Animal/Plant Cells"; by: K. Chun et al.; Proceedings of 12th International Workshop on Micro Electro Mechanical Systems (MEMS); Jan. 1999; Abstract Only.
	1S	"Deep Etching Key to the MEMS/MST Revolution"; by: Prashant Gadil; R & D; July 1998; p. 38.

EXAMINER <i>Deegan Jr.</i>	DATE CONSIDERED <i>7/2005</i>
-------------------------------	----------------------------------

PATENT APPLICATION

Sheet 2 of 5

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 200210175-1	APPLICATION NO. 10/619 639	CONFIRMATION NO.
	APPLICANT Martha A. Truning et al.		
	FILING DATE Herewith 7/15/2003	GROUP Unk.	2853

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
2A	6,008,138	12/1999	Laermer et al.	—
2B	6,045,710	04/2000	Silverbrook	—
2C	6,081,635	06/2000	Hehmann	—
2D	6,096,656	08/2000	Matzke et al.	—
2E	6,139,761	10/2000	Ohkuma	—
2F	6,305,080	10/2001	Komuro et al.	—
2G	5,124,717	06/1992	Campanelli et al.	—
2H	5,141,596	08/1992	Hawkins et al.	—
2I	6,481,832	11/19/2002	Liu et al.	—
2J				
2K				

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
2L	DE19538103A1	04/1997	Bosch GMBH	—	
2M	GB2245366A	01/1992	Bosch GMBH	—	
2N	GB 2290413A	12/1995	Bosch GMBH	—	
2O	GB 2341348A	03/2000	Bosch GMBH	—	
2P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

2Q	"Anisotropic Silicon Etch Characterization in the TFTL STS Etcher"; August 20, 1999; pp: 1-5.
2R	"Etching Characteristics And Profile Control in a Time Multiplexed Inductively Coupled Plasma Etcher"; by: AA Ayon, CC Lin, RA Braff & MA Schmidt of the Department of Electrical Engineering and Computer Science (EECS); Solid-State Sensor and Actuator Workshop, Hilton Head Island, SC; June 8-11, 1998; pp: 41-44.
2S	"Characterization of a Time Multiplexed Inductively Coupled Plasma Etcher"; by: AA Ayon, R Braff, CC Lin, HH Sawin & MA Schmidt; Journal of the Electrochemical Society; 146 (1); 1999; pp: 339-349.

EXAMINER <i>Boeger/B</i>	DATE CONSIDERED <i>2/2005</i>
-----------------------------	----------------------------------

PATENT APPLICATION

Sheet 3 of 5

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 200210175-1	APPLICATION NO. 10/69639	CONFIRMATION NO.
	APPLICANT Martha A. Truninger et al.		
	FILING DATE Herewith 7/15/2003	GROUP Unknown	2853

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
3A				
3B				
3C				
3D				
3E				
3F				
3G				
3H				
3I				
3J				
3K				

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
3L					
3M					
3N					
3O					
3P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

<i>DC</i>	3Q	STS-Surface Technology Systems-1st ASE Users Meeting, pp. 1-10; Advanced Silicon Etch, pp. 1-28; Technology Review, pp. 1-10; California, 1997.
<i>DC</i>	3R	"High-Aspect-Ratio Si Etching for Microsensor Fabrication"; by: WH Juan & SW Pang; Journal of Vacuum Science & Technology A; Vol. 13, No. 3; 1995; pp: 834-838.
<i>DC</i>	3S	"Bosch Deep Silicon Etching: Improved Uniformity and Etch Rate for Advanced MEMS Applications"; by: F Laermer et al.; 0-7803-5194-00; 1999; pp. 211-216.

EXAMINER <i>Roger S. H.</i>	DATE CONSIDERED <i>8/2005</i>
------------------------------------	--------------------------------------

PATENT APPLICATION

Sheet 4 of 5

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 200210175-1	APPLICATION NO. 10/619639	CONFIRMATION NO.
	APPLICANT Martha A. Truninger et al.		
	FILING DATE Herewith 7/15/03	GROUP Unkn.	2853

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
4A				
4B				
4C				
4D				
4E				
4F				
4G				
4H				
4I				
4J				
4K				

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
4L					
4M					
4N					
4O					
4P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

<i>[Signature]</i>	4Q	"Advanced Silicon Etching Using High Density Plasmas"; by: JK Bhardwaj & H Ashraf; SPIE-Society of Photo-Optical Instrumentation Engineers; Vol. 2639; October 1995; pp 224-233.
<i>[Signature]</i>	4R	"Recent Advances in Silicon Etching for MEMS Using the ASE Process"; by: AM Hynes et al.; Sensors And Actuators; Vol. 74; 1999; pp 13-17.
<i>[Signature]</i>	4S	"Fabrication of Thick Silicon Dioxide Layers Using DRIE, Oxidation and Trench Refill"; by: C Zhang & K Najafi; Proceedings of 15th IEEE International Conference on Micro Electro Mechanical Systems; Jan. 20-24, 2002; pp. 160-163.

EXAMINER <i>[Signature]</i>	DATE CONSIDERED <i>7/20/05</i>
------------------------------------	---------------------------------------

PATENT APPLICATION

Sheet 5 of 5

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO.	APPLICATION NO.	CONFIRMATION NO.
	200210175-1	10/69639	
	APPLICANT		
	Martha A. Truninger et al.	FILING DATE	GROUP
	7/5/03	2853	

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
5A				
5B				
5C				
5D				
5E				
5F				
5G				
5H				
5I				
5J				
5K				

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
5L					
5M					
5N					
5O					
5P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	5Q	"Fabrication of Out-of-Plane Curved Surfaces in Si by Utilizing RIE Lag"; by: TA Chou & K Najafi; Proceedings of 15th IEEE International Conference on Micro Electro Mechanical Systems; Jan. 20-24, 2002; pp. 145-148.
	5R	
	5S	

EXAMINER

DATE CONSIDERED

2/2005